

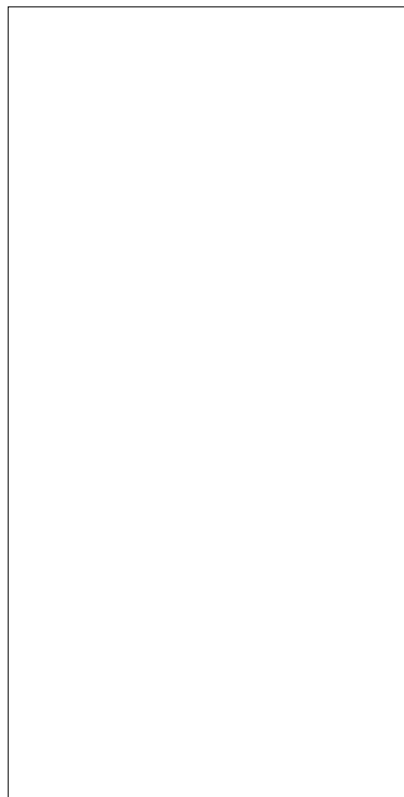


## JCT1055Z 55A SCR

Rev.A.1.1

### DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1055Z SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1055Z provides a rated insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.



### MAIN FEATURES

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	
Operating junction temperature range	T <sub>j</sub>	-40-125	
Repetitive peak off-state voltage (T <sub>j</sub> =25 °C)	V <sub>DRM</sub>	1000	V
Repetitive peak reverse voltage (T <sub>j</sub> =25 °C)	V <sub>RRM</sub>	1000	V
Average on-state current (T <sub>c</sub> 60 °C)	I <sub>T(AV)</sub>	35	A
RMS on-state current (T <sub>c</sub> 60 °C)	I <sub>T(RMS)</sub>	55	A
Non repetitive surge peak on-state current (t <sub>p</sub> =10ms, T <sub>j</sub> =25 °C)	I <sub>TSM</sub>	700m	m
Non repetitive surge peak on-state current (t <sub>p</sub> =8.3ms, T <sub>j</sub> =25 °C)			

Q f o T Q t04 0 Td ( ) Tj F ) 7 (s1Tj1616 12j.72 A

Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	10	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W

**ORDERING INFORMATION**

J CT 10 55 Z

FIG.1: Maximum power dissipation versus RMS on-state current

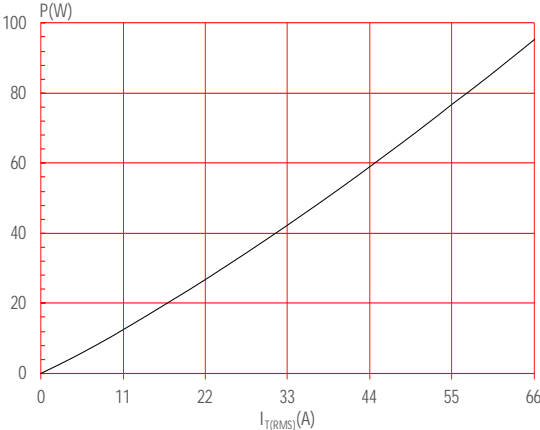
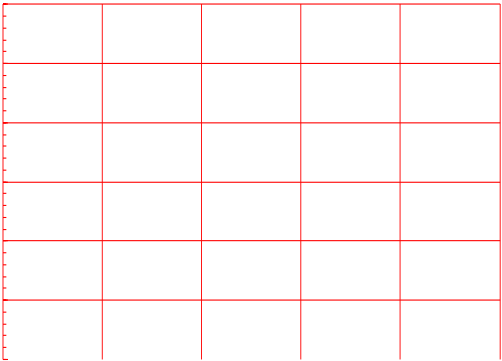


FIG.2: RMS on-state current versus case temperature



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 **JieJie Microelectronics Co., Ltd.**

**ORDERING INFO**

Order code	IGT(mA)	PackC	0.775.6.48 539.0 10.56 70.46 3.4 r11.48 563.32 7
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